

REMARKS

Claims 26-32 are pending in this application. By this Amendment, claims 1-25 are canceled without prejudice to, or disclaimer of, the subject matter recited in those claims. Claims 26-32 are added. Claims 26-32 add no new matter as will be discussed in detail below. Reconsideration of the application based on the above amendments and the following remarks is respectfully requested.

The Office Action, in paragraph 4, again withdraws claims 7, 11 and 17 from consideration. The cancellation of claims 7, 11 and 17 renders this action moot.

The Office Action, in paragraph 6, rejects claims 1-6, 8-10, 12-16 and 18-25 under 35 U.S.C. §103(a) as being unpatentable over U.S. Patent No. 5,824,186 to Smith et al. (hereinafter "Smith"), Applicants' alleged prior art admissions, and WO 99/12170 (hereinafter "WO '170"), all as applied in previous Office Actions, and further in view of Brown et al., "Nonvolatile Semiconductor Memory Technology: A Comprehensive Guide to Understanding Using NVSM Devices," 1998, IEEE Press, pp. 464-465 (hereinafter "Brown"). The Office Action, in paragraph 7, rejects claims 1-4, 8-10, 12-14 , 19, 20 and 22 under 35 U.S.C. §103(a) as being unpatentable over Applicants' alleged prior art admissions and WO '170 and Brown, all as applied to the claims above, and further in view of Japanese Patent No. JP 8-167703 (hereinafter "JP '703"). The Office Action in paragraph 8, rejects claims 5, 6, 15, 21 and 23-25 under 35 U.S.C. §103(a) as being unpatentable over Applicant's alleged prior art admissions, WO '170, Brown and JP '703 as applied to the claims above and further in view of Japanese Patent No. JP 5-275611 (hereinafter "JP '611"). The cancellation of the enumerated claims renders these rejections moot.

Insofar, as the subject matter recited in any of the above enumerated claims is incorporated into the new claims 26-32, these claims 26-32 recite additional features which distinguish the subject matter of these claims over the previously applied references.

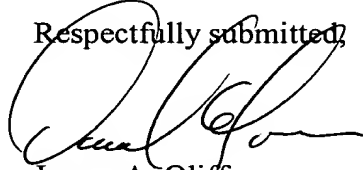
Claims 26 recites, among other features, a ferroelectric memory, wherein first and second recess portions are formed in the substrate, and the first microstructure is provided in the first recess portion and the second microstructure is provided in the second recess portion. Claim 26 introduces no new matter because it combines features of previous claims 3 and 5 with the additional feature recited above regarding recess portions. Support for the above-recited feature is included in the specification at least at paragraph [0071], and in Fig. 11. Claim 32 recites, among other features, a ferroelectric memory, wherein a second recess portion is formed in the substrate, the second microstructure is larger than the first microstructure and provided in the second recess portion, a first recess portion is formed in the second microstructure and the first microstructure is provided in the first recess portion of the second microstructure. Claim 32 introduces no new matter as it is supported at least by claim 10 as previously filed and paragraph [0023] of the specification. Dependent claims 27-31 also introduce no new matter in that they are supported by at least Figs. 10, 11, 22 and 23, and the descriptions of those Figures in the specification.

Applicants respectfully submit that the combination of the applied references fails to disclose, or even to have suggested, the specific combinations of features recited in new claims 26-32. Additionally, as noted at paragraph [00141] of the specification, positioning the microstructure in recess portions formed in a substrate will remove, or at least decrease, certain limitations in the fabrication process of the disclosed memory components and allow a plurality of microstructures to be mounted on a substrate simultaneously.

In view of the foregoing, Applicants respectfully submit that this application is in condition for allowance. Favorable consideration and prompt allowance of claims 26-32 are earnestly solicited.

Should the Examiner believe that anything further would be desirable in order to place this application in even better condition for allowance, the Examiner is invited to contact Applicants' undersigned representative at the telephone number set forth below.

Respectfully submitted,



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